NPN power transistors BD135; BD137; BD139

FEATURES

- High current (max. 1.5 A)
- Low voltage (max. 80 V).

APPLICATIONS

- Driver stages in hi-fi amplifiers and television circuits.

DESCRIPTION

NPN power transistor in a TO-126; SOT32 plastic package. PNP complements: BD136, BD138 and BD140.

PINNING

PIN	DESCRIPTION
1	emitter
2	collector, connected to metal part of mounting surface
3	base

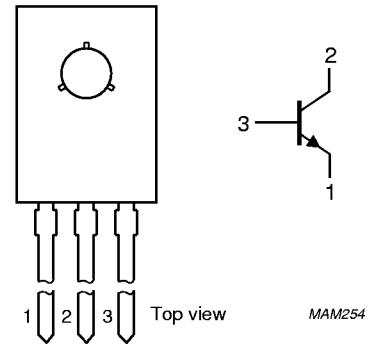


Fig.1 Simplified outline (TO-126; SOT32) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BD135		–	45	V
	BD137		–	60	V
	BD139		–	100	V
V_{CEO}	collector-emitter voltage	open base			
	BD135		–	45	V
	BD137		–	60	V
	BD139		–	80	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	1.5	A
I_{CM}	peak collector current		–	2	A
I_{BM}	peak base current		–	1	A
P_{tot}	total power dissipation	$T_{mb} \leq 70$ °C	–	8	W
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	100	K/W
$R_{th\ j\text{-}mb}$	thermal resistance from junction to mounting base		10	K/W

Note

1. Refer to TO-126; SOT32 standard mounting conditions.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = 30 V	–	–	100	nA
		I_E = 0; V_{CB} = 30 V; T_j = 125 °C	–	–	10	μA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = 5 V	–	–	100	nA
h_{FE}	DC current gain	V_{CE} = 2 V; (see Fig.2)				
		I_C = 5 mA	40	–	–	
		I_C = 150 mA	63	–	250	
		I_C = 500 mA	25	–	–	
	DC current gain	I_C = 150 mA; V_{CE} = 2 V; (see Fig.2)				
	BD135-10; BD137-10; BD139-10		63	–	160	
	BD135-16; BD137-16; BD139-16		100	–	250	
V_{CEsat}	collector-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA	–	–	0.5	V
V_{BE}	base-emitter voltage	I_C = 500 mA; V_{CE} = 2 V	–	–	1	V
f_T	transition frequency	I_C = 50 mA; V_{CE} = 5 V; f = 100 MHz	–	190	–	MHz
$\frac{h_{FE1}}{h_{FE2}}$	DC current gain ratio of the complementary pairs	$\lvert I_C \rvert$ = 150 mA; $\lvert V_{CE} \rvert$ = 2 V	–	1.3	1.6	

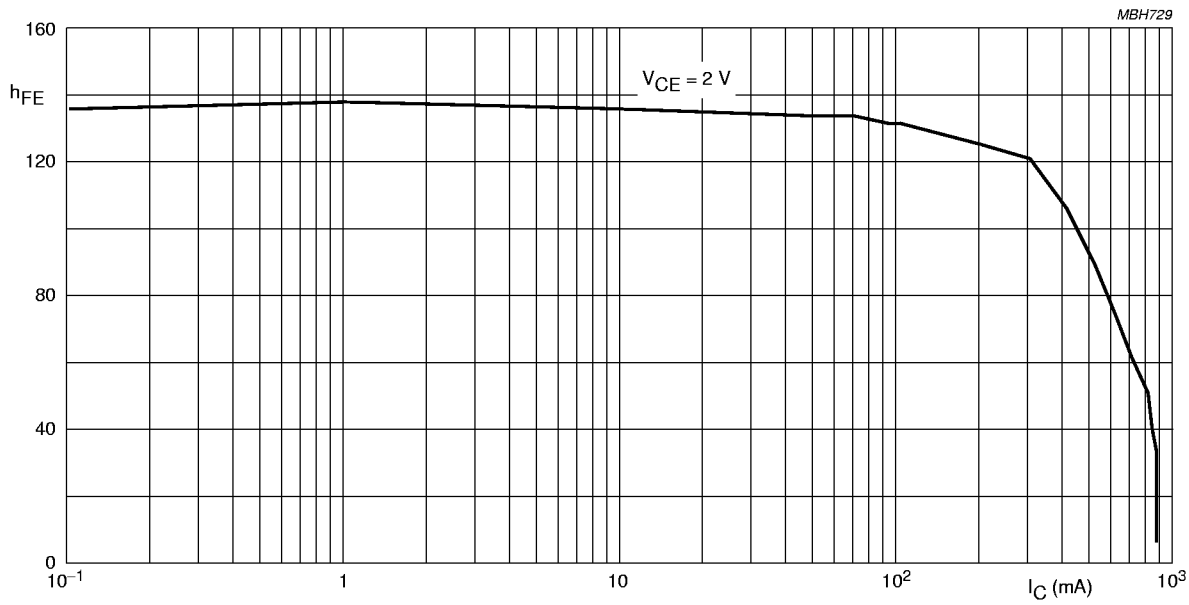
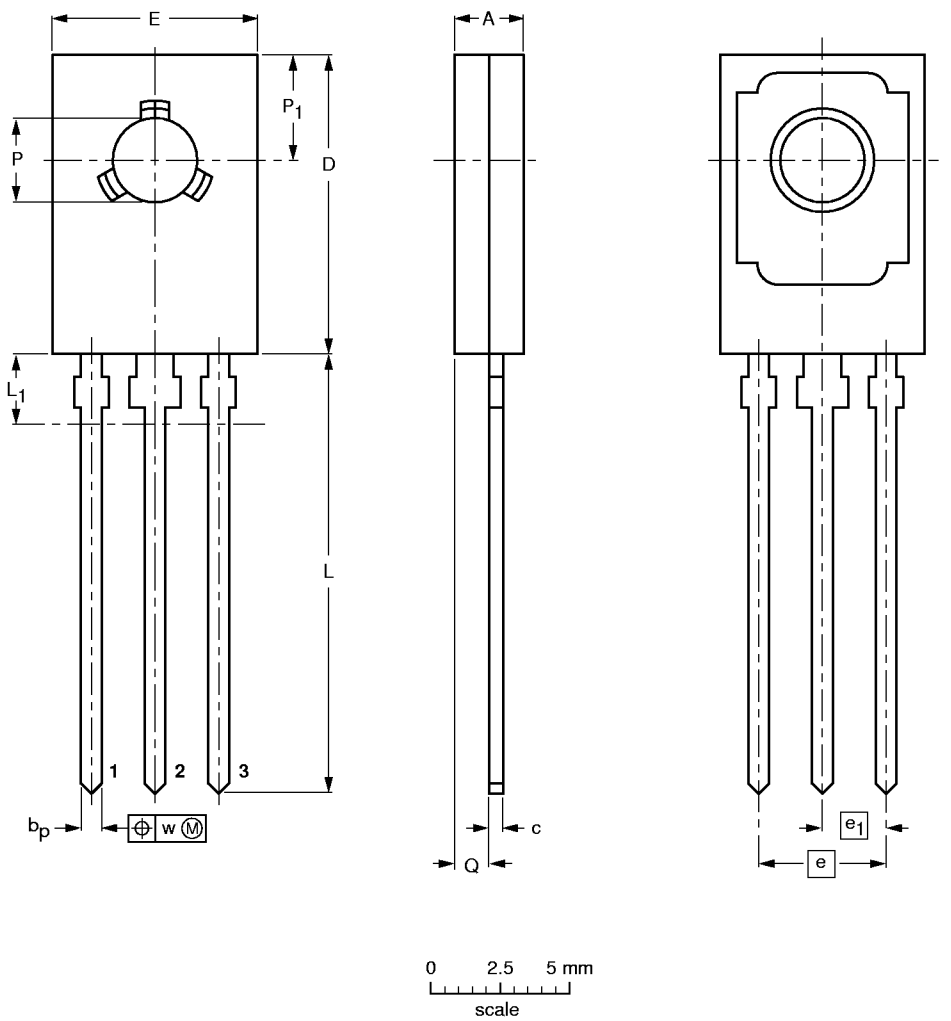


Fig.2 DC current gain; typical values.

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; mountable to heatsink, 1 mounting hole; 3 leads SOT32



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_p	c	D	E	e	e_1	L	L_1(1) max	Q	P	P_1	w
mm	2.7 2.3	0.88 0.65	0.60 0.45	11.1 10.5	7.8 7.2	4.58	2.29	16.5 15.3	2.54	1.5 0.9	3.2 3.0	3.9 3.6	0.254

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT32		TO-126				97-03-04